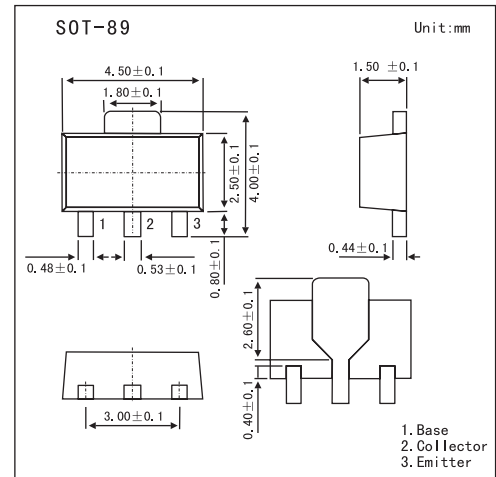


PNP Medium Power Transistor

BC869

■ Features

- High current.
- Three current gain selections.
- 1.2 W total power dissipation.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-32	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-1	A
Peak collector current	I_{CM}	-2	A
Peak base current	I_{BM}	-200	mA
Total power dissipation	P_{tot}	*1 and *2	0.5
		*1 and *3	0.85
		*1 and *4	1.2
Storage temperature	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	R_{amb}	-65 to +150	$^\circ\text{C}$
Thermal resistance from junction to ambient	$R_{th(j-a)}$	*1 and *2	250
		*1 and *3	147
		*1 and *4	104
Thermal resistance from junction to solder point	$R_{th(j-s)}$	20	K/W

*1.Refer to SOT89 standard mounting conditions.

*2.Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated footprint.

*3.Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 1 cm^2 .

*4.Device mounted on an FR4 printed-circuit board, single-sided copper, tin-plated, mounting pad for collector 6 cm^2 .

BC869■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter		Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current		ICBO	$V_{CB} = -25\text{ V}, I_E = 0$			-100	nA
			$V_{CB} = -25\text{ V}, I_E = 0; T_j = 25^\circ\text{C}$			-10	μA
Emitter cutoff current		IEBO	$V_{EB} = -5\text{ V}, I_C = 0$			-100	nA
DC current gain	BC868	hFE	$I_C = -5\text{ mA}; V_{CE} = -10\text{ V}$	50			
			$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$	85		375	
			$I_C = -1\text{ A}; V_{CE} = -1\text{ V}$	60			
	BC868-16	hFE	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$	100		250	
	BC869-25	hFE	$I_C = -500\text{ mA}; V_{CE} = -1\text{ V}$	160		375	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = -1\text{ A}; I_B = -100\text{ mA}$			-500	mV
Base to emitter voltage		V_{BE}	$I_C = -5\text{ mA}; V_{CE} = -10\text{ V}$			-700	mV
			$I_C = -1\text{ A}; V_{CE} = -1\text{ V}$			-1	V
Collector capacitance		C_c	$I_E = I_C = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$		28		pF
Transition frequency		f_t	$I_C = -50\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	40	140		MHz

■ hFE Classification

TYPE	BC869	BC869-16	BC869-25
Marking	CEC	CGC	CHC